

#### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

#### 3. Applications

- DC to DC conversion
- High-speed line driver
- Low-side load switch
- Switching circuits

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	-	26	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	-	19	W
Static chara	cteristics		- I				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C		-	13	16	mΩ



# 5. Pinning information

Table 2	. Pinning info	ormation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G (→ 云本)
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	s
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

#### Table 3. Ordering information

Type number	nber Package					
	Name	Description	Version			
BUK4D16-20		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK4D16-20	6L

20 V, N-channel Trench MOSFET

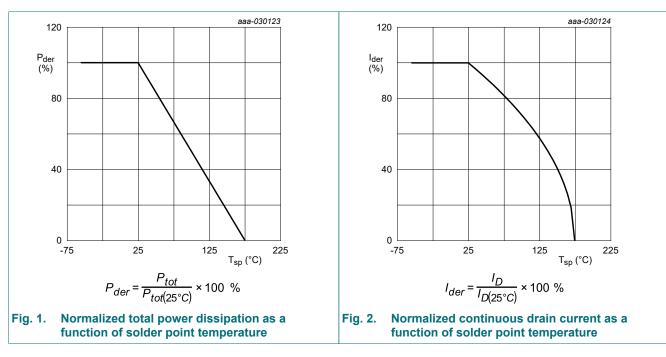
### 8. Limiting values

#### Table 5. Limiting values

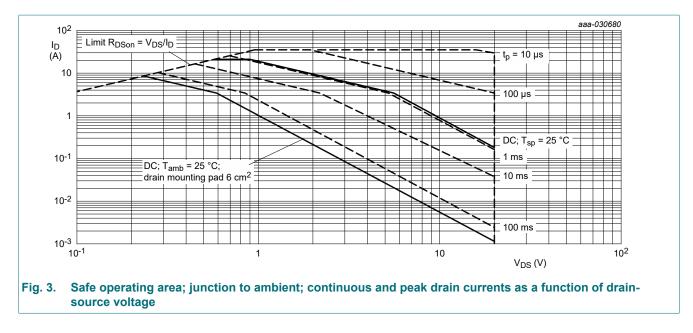
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	26	Α
		V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 100 °C		-	17	A
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	8.5	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	106	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	19	W
		T <sub>amb</sub> = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode		•			
ls	source current	T <sub>sp</sub> = 25 °C		-	19	А
		T <sub>amb</sub> = 25 °C	[1]	-	2	А
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	75	А
ESD maximu	um rating		•			
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2000	V
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.3 A; DUT in v avalanche (unclamped)		-	13	mJ
	I	1				

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
 Measured between all pins.



#### 20 V, N-channel Trench MOSFET

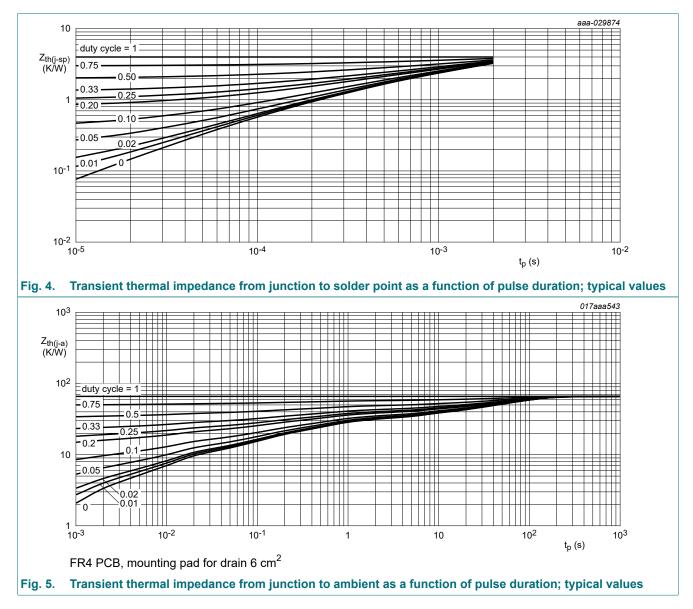


BUK4D16-20

# 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	8	K/W

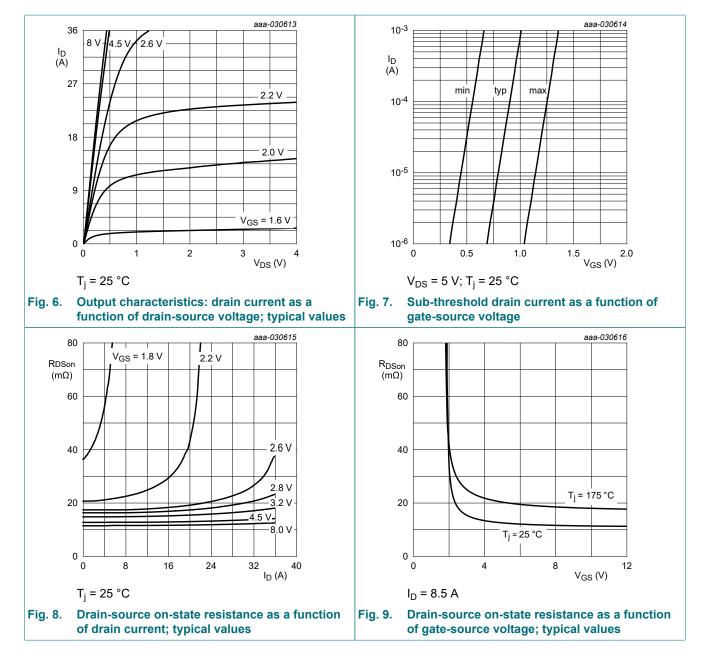
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



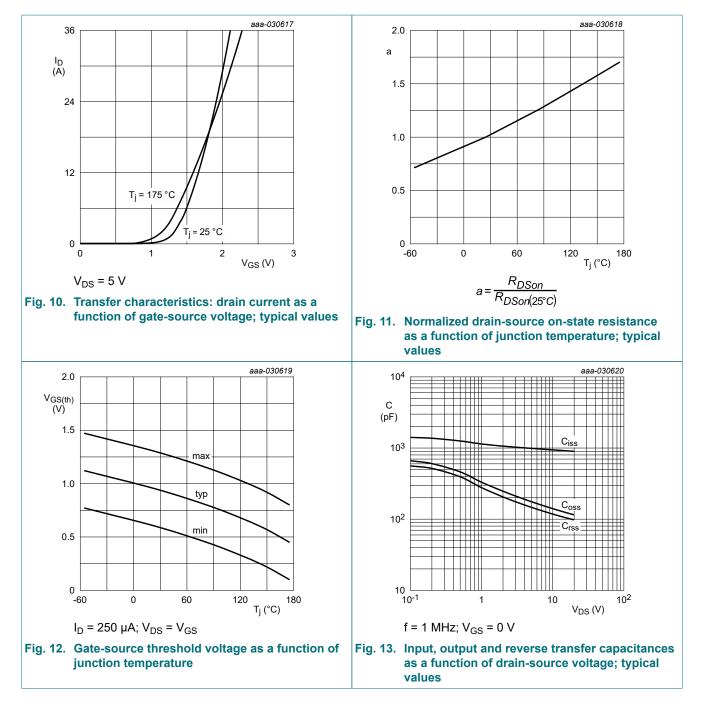
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	1				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.6	0.95	1.3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	20	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 8 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	11	14	mΩ
		V <sub>GS</sub> = 8 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 175 °C	-	19	24	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C	-	13	16	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	17	21	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C	-	14.4	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic ch	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9 A; V <sub>GS</sub> = 4.5 V;	-	9.8	15	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	931	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	144	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	121	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 9 A; V <sub>GS</sub> = 4.5 V;	-	4	-	ns
r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
d(off)	turn-off delay time		-	15	-	ns
f	fall time		-	9	-	ns
Source-drai	n diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
rr	reverse recovery time	$I_{S} = 2 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	10	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 10 V; T <sub>j</sub> = 25 °C	-	3	-	nC

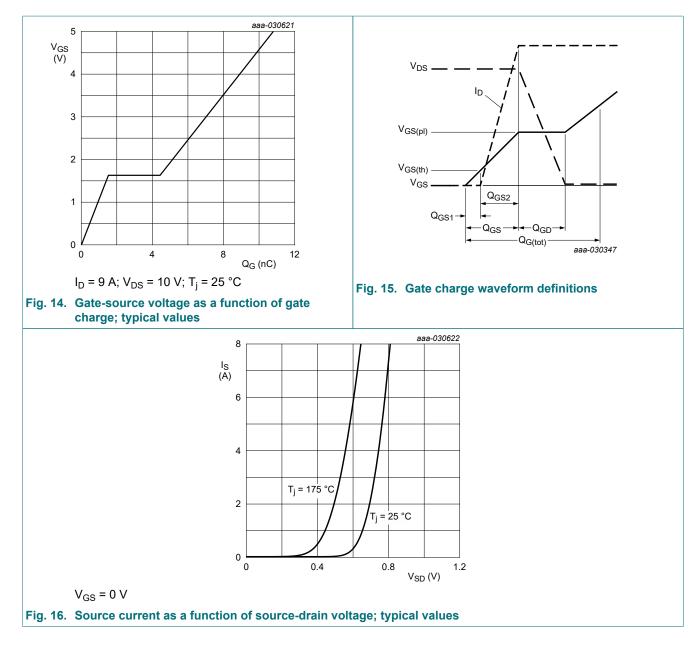
#### 20 V, N-channel Trench MOSFET



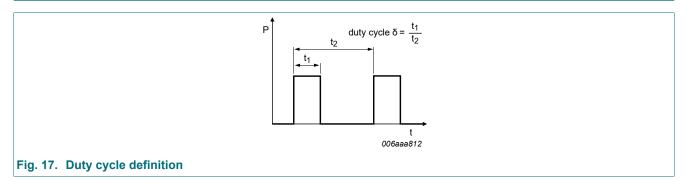
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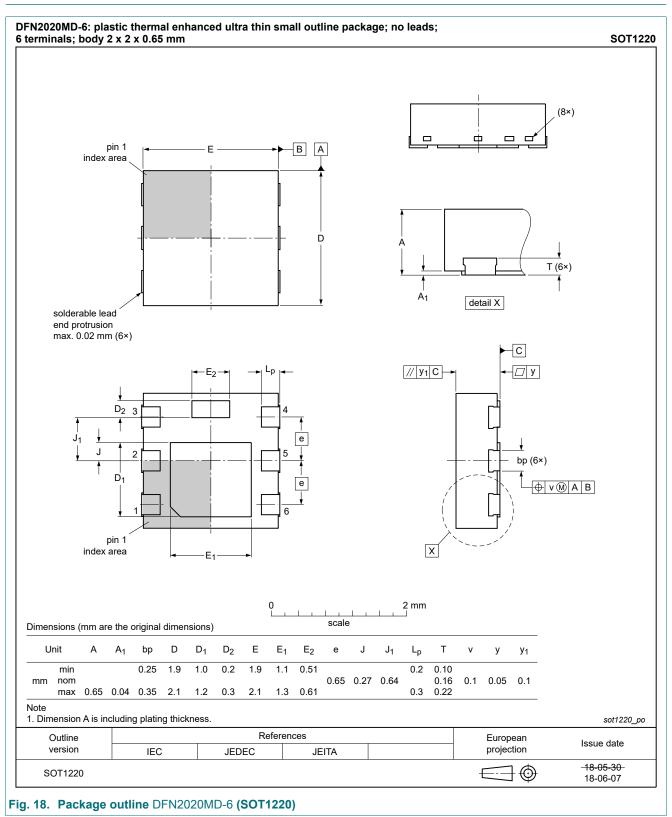
# **11. Test information**



#### **Quality information**

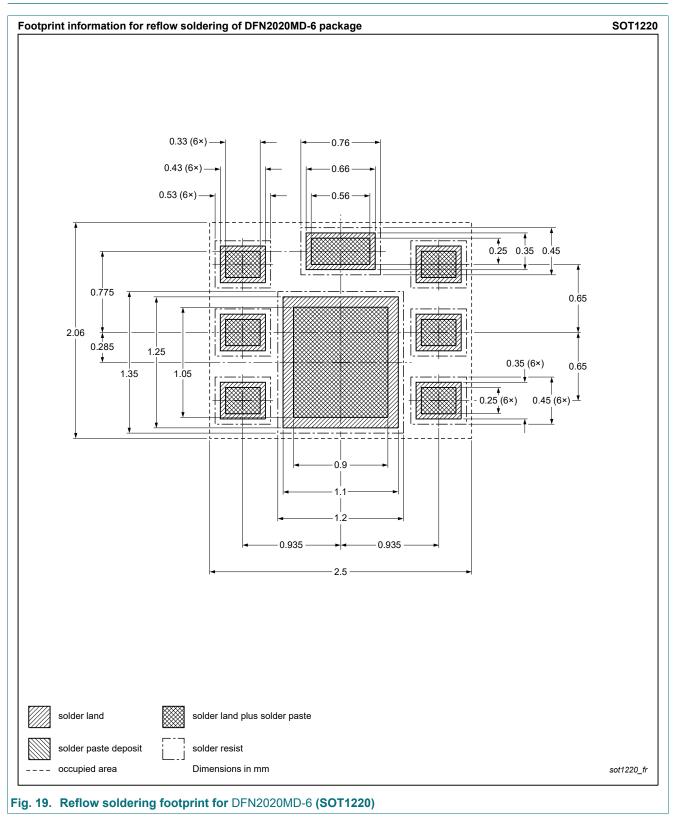
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



#### 20 V, N-channel Trench MOSFET

### 13. Soldering



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
BUK4D16-20. v.2	20200709	Product data sheet	-	BUK4D16-20. v.1		
Modifications:	Product status change	ged.				
BUK4D16-20. v.1	20200114	Objective data sheet	-	-		

#### 20 V, N-channel Trench MOSFET

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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